

IN THE CLAIMS:

Please amend claims 1, 4, 10, 19, 32, 45, 68 and 71 as follows. Attached hereto is a marked-up copy of the amended claims

Sub C1

1. (Twice Amended) A semiconductor device comprising:  
a first substrate having an insulating surface;  
a second substrate opposing said first substrate;  
at least one thin film transistor formed on said insulating surface, said thin film transistor having a polycrystalline semiconductor layer comprising source, drain and channel regions;  
an interlayer insulating film comprising an inorganic material formed on said thin film transistor;  
an organic resin film provided over said interlayer insulating film; and  
a pixel electrode formed over said organic resin film and connected to said thin film transistor through an opening provided in said organic resin film,  
wherein said polycrystalline semiconductor layer exhibits a peak of Raman spectra, displaced from a peak of single crystalline silicon to the lower frequency direction.

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4. (Amended) A device according to claim 1 wherein said channel region comprises a material selected from the group consisting of silicon, germanium and a combination thereof.

Sub D2

B4

10. (Twice Amended) A semiconductor device comprising:  
a first substrate having an insulating surface;  
a second substrate opposing said first substrate;  
at least one thin film transistor formed on said insulating surface, said thin film transistor having a polycrystalline semiconductor layer comprising source, drain and channel regions;  
an interlayer insulating film comprising an inorganic material formed on said thin film transistor;  
an organic resin film provided over said interlayer insulating film; and  
a pixel electrode formed over said organic resin film and connected to said thin

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B4

film transistor through an opening provided in said organic resin film,  
wherein said polycrystalline semiconductor layer exhibits a peak of Raman  
spectra, displaced from 522  $\text{cm}^{-1}$  to the lower frequency direction, and  
wherein said polycrystalline semiconductor layer is formed by crystallizing an  
amorphous semiconductor layer.

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C3

B5

19. (Twice Amended) A semiconductor device comprising:  
a first substrate having an insulating surface;  
a second substrate opposing said first substrate;  
at least one thin film transistor formed on said insulating surface, said thin film  
transistor comprising:  
a polycrystalline semiconductor layer having source, drain and channel regions;  
a gate insulating layer adjacent to said channel region; and  
a gate electrode adjacent to said channel region;  
an interlayer insulating film comprising an inorganic material formed on said thin  
film transistor; and  
an organic resin film provided over said interlayer insulating film;  
wherein said polycrystalline semiconductor layer exhibits a peak of Raman  
spectra, displaced from a peak of single crystalline silicon to the lower frequency direction.

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D4

B6

32. (Twice Amended) A semiconductor device comprising:  
a first substrate having an insulating surface;  
a second substrate opposing said first substrate;  
at least one thin film transistor formed on said insulating surface, said thin film  
transistor comprising:  
a polycrystalline semiconductor layer having source, drain and channel regions;  
a gate insulating layer adjacent to said channel region;  
an interlayer insulating film comprising an inorganic material formed on said thin  
film transistor; and  
an organic resin film provided over said thin film transistor and said interlayer  
insulating film;

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B6  
wherein said polycrystalline semiconductor layer comprises silicon and exhibits a peak of Raman spectra, displaced from  $522\text{ cm}^{-1}$  to the lower frequency direction, and  
wherein said polycrystalline semiconductor layer is formed by crystallizing an amorphous semiconductor layer.

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C37  
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45. (Twice Amended) A semiconductor device comprising:  
a first substrate having an insulating surface;  
a second substrate opposing said first substrate;  
at least an n-channel thin film transistor and at least a p-channel thin film transistor both formed over said first substrate, each of said n-channel and p-channel thin film transistors comprising:  
a polycrystalline semiconductor layer having source, drain and channel regions;  
a gate insulating layer adjacent to said channel region; and  
a gate electrode adjacent to said channel region;  
an interlayer insulating film comprising an inorganic material formed on said thin film transistor; and  
an organic resin film provided over said interlayer insulating film;  
wherein said polycrystalline semiconductor layer exhibits a peak of Raman spectra, displaced from a peak of single crystalline silicon to the lower frequency direction.

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B8  
68. (Amended) A semiconductor device comprising:  
a first substrate having an insulating surface;  
a second substrate opposing said first substrate;  
at least one thin film transistor formed on said insulating surface, said thin film transistor comprising:  
a polycrystalline semiconductor layer having source, drain and channel regions;  
an interlayer insulating film comprising an inorganic material formed on said thin film transistor; and  
an organic resin film provided over said interlayer insulating film;  
a pixel electrode provided over said organic resin film and connected to said thin film transistor through an opening provided in said organic resin film;

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B8 wherein said polycrystalline semiconductor layer exhibits a peak of Raman spectra, displaced from  $522\text{ cm}^{-1}$  to the lower frequency direction, and

wherein said polycrystalline semiconductor layer is formed by crystallizing an amorphous semiconductor layer.

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B9 71. (Amended) A device according to claim 68 wherein said channel region comprises a material selected from the group consisting of silicon, germanium and a combination thereof.

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